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(54) **Title**: A PROCESS FOR THE MANUFACTURE OF SEMICONDUCTOR DEVICES COMPRISING THE CHEMICAL MECHANICAL POLISHING (CMP) OF III-V MATERIAL IN THE PRESENCE OF A CMP COMPOSITION COMPRISING A SPECIFIC NON-IONIC SURFACTANT

(57) **Abstract**: A process for the manufacture of semiconductor devices comprising the chemical-mechanical polishing of a substrate or layer containing at least one lll-V material in the presence of a chemical-mechanical polishing composition (Q1) comprising (A) inorganic particles, organic particles, or a mixture or composite thereof, (B) at least one amphiphilic non-ionic surfactant having (b1) at least one hydrophobic group; and (b2) at least one hydrophilic group selected from the group consisting of polyoxyalkylene groups comprising (b22) oxyalkylene monomer units other than oxyethylene monomer units; and (M) an aqueous medium.